TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM2LZ47

AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off–State Voltage : $V_{DRM} = 800V$ • R.M.S. On–State Current : $I_{T (RMS)} = 2A$

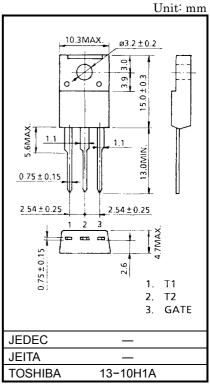
• High Commutation (dv / dt) : $(dv / dt) c = 5V / \mu s$ (Min.) • Isolation Voltage : $V_{ISOL} = 1500V$ AC

MAXIMUM RATINGS

| CHARACTERISTIC | SYMBOL | RATING | UNIT | |
|---|----------------------|------------|------------------|--|
| Repetitive Peak Off-State Voltage | V_{DRM} | 800 | V | |
| R.M.S. On-State Current (Full Sine Waveform) | I _{T (RMS)} | 2 | А | |
| Peak One Cycle Surge On-State | l | 8 (50Hz) | Α | |
| Current (Non-Repetitive) | ITSM | 8.8 (60Hz) | | |
| I ² t Limit Value | I ² t | 0.32 | A ² s | |
| Critical Rate of Rise of On-State Current (Note) | di / dt | 50 | A/μs | |
| Peak Gate Power Dissipation | P_{GM} | 3 | W | |
| Average Gate Power Dissipation | P _{G (AV)} | 0.3 | W | |
| Peak Gate Voltage | V_{FGM} | 10 | V | |
| Peak Gate Current | I _{GM} | 1.6 | Α | |
| Junction Temperature | Tj | -40~125 | °C | |
| Storage Temperature Range | T _{stg} | -40~125 | °C | |
| Isolation Voltage (AC, t = 1min.) | V _{ISOL} | 1500 | V | |

Note: di / dt test condition

 V_{DRM} = 400V, $I_{TM} \le 3A$, $t_{gw} \ge 10\mu s$, $t_{gr} \le 250ns$, $i_{gp} = I_{GT} \times 2.0$

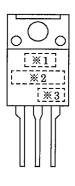


Weight: 1.7g

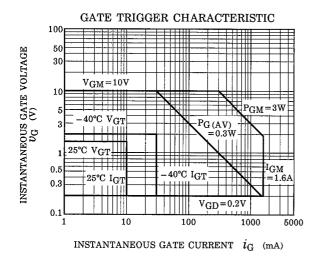
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

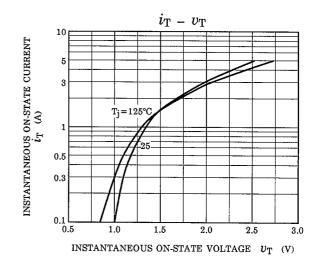
| CHARACTERISTIC | | SYMBOL | L TEST CONDITION | | MIN | TYP. | MAX | UNIT |
|--|--|-----------------------|---|-------------------|-----|------|-----|--------|
| Repetitive Peak Off-State Current | Repetitive Peak Off-State Current I _{DRM} V _{DRM} = 800V | | _ | _ | 20 | μΑ | | |
| Gate Trigger Voltage | I | | V _D = 12V, R _I = 20Ω | T2 (+), Gate (+) | _ | _ | 1.5 | V |
| | Ш | V_{GT} | | T2 (+) , Gate (−) | _ | _ | 1.5 | |
| | III | | _ | T2 (-) , Gate (-) | _ | _ | 1.5 | |
| Gate Trigger Current | I | | V _D = 12V, R _L = 20Ω | T2 (+) , Gate (+) | _ | _ | 10 | mA |
| | II | I_{GT} | | T2 (+) , Gate (−) | _ | _ | 10 | |
| | III | | | T2 (-) , Gate (-) | _ | _ | 10 | |
| Peak On-State Voltage | | V_{TM} | I _{TM} = 3A | | _ | _ | 2.0 | V |
| Gate Non-Trigger Voltage | | V_{GD} | V _D = 800V, Tc = 125°C | | 0.2 | _ | _ | V |
| Holding Current | | lΗ | V _D = 12V, I _{TM} = 1A | | _ | _ | 10 | mA |
| Thermal Resistance | | R _{th (j−a)} | Junction to Ambient, AC | | _ | _ | 58 | °C/W |
| Critical Rate of Rise of Off-State Voltage | | dv / dt | V _{DRM} = 800V, T _j = 125°C Exponential Rise | | - | 500 | - | V / µs |
| Critical Rate of Rise of Off-State Voltage at Communication (dv / dt) of | | (dv / dt) c | V_{DRM} = 400V, T_j = 125°C (di / dt) c = -0.5A / ms | | 5 | _ | _ | V / µs |

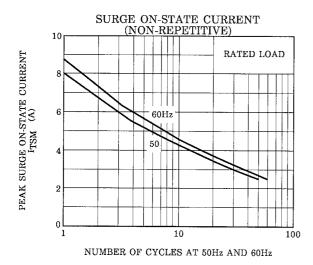
MARKING

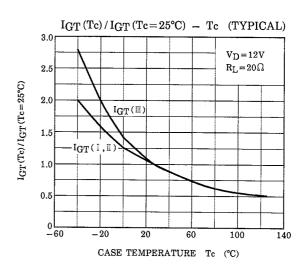


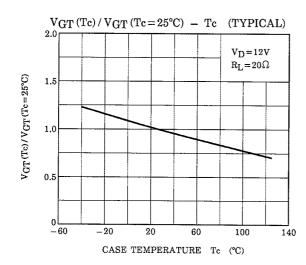
| NUMBER | | SYMBOL | MARK |
|--------|---|---------|--|
| *1 | Toshiba Product Mar | k | 5 |
| *2 | TYPE | SM2LZ47 | M2LZ47 |
| *3 | Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year) | | Example 8A : January 1998 8B : February 1998 8L : December 1998 |

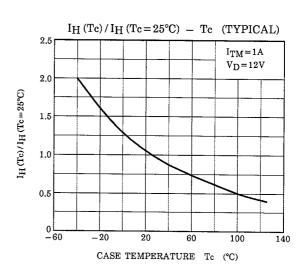




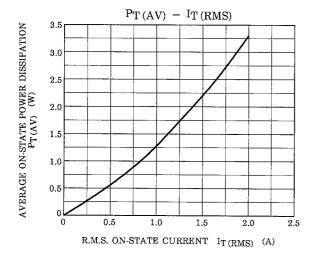


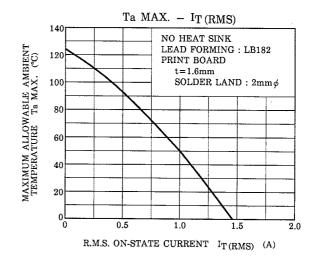


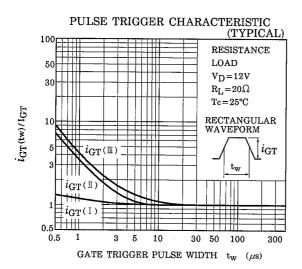


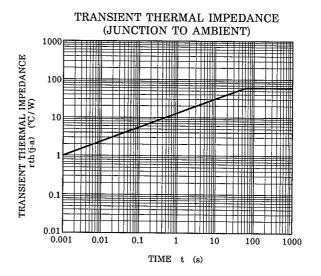


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